



◆ Absolute Maximum Ratings ( $T_c=25^{\circ}\text{C}$ )

Symbol	Parameters	Ratings	Unit	
VCBO	Collector-Base Voltage 集电极 - 基极电压	100	V	
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	100	V	
VEBO	Emitter-Base Voltage 发射极 - 基极电压	7	V	
$I_C$	Collector Current-Continuous 集电极连续电流	6	A	
$I_B$	Base Current-Continuous 基极连续电流	2.0	A	
PC	Collector Power Dissipation 耗散功率	65	W	
$T_j$	Max.Operating junction temperature 最大结温	150	$^{\circ}\text{C}$	
$T_{stg}$	Storage Temperature 存储温度	-65 ~ +150	$^{\circ}\text{C}$	

**◆ Electrical characteristics (Tc=25°C unless otherwise noted)**

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I <sub>CBO</sub>	Collector Cutoff Current 集电极截止电流	--	--	<b>1</b>	uA	V <sub>CE</sub> =100V, V <sub>EB</sub> =0
I <sub>EBO</sub>	Emitter Cutoff Current 发射极截止电流	--	--	<b>1.0</b>	uA	V <sub>BE</sub> =10V, I <sub>C</sub> =0
BV <sub>CEO</sub>	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	<b>100</b>	--	--	V	I <sub>C</sub> =30mA, I <sub>B</sub> =0
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压	--	--	<b>1.5</b>	V	I <sub>C</sub> =4A, I <sub>B</sub> =0.4A
h <sub>FE</sub>	DC Current Gain(Note 1) 直流电流增益	<b>80</b>	--	<b>160</b>		I <sub>C</sub> =1A, V <sub>CE</sub> =5V
f <sub>T</sub>	Current-Gain—Bandwidth 电流增益带宽	<b>10.0</b>	--	--	MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A, f=1MHz

Note 1: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.